

# Masao Sakuraba

## List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Learning Rule for a Quantum Neural Network Inspired by Hebbian Learning. IEICE Transactions on Information and Systems, 2021, E104.D, 237-245.	0.4	2
2	Electron-cyclotron resonance Ar plasma-induced electrical activation of B atoms without substrate heating in B doped Si epitaxial films on Si(100). Materials Science in Semiconductor Processing, 2020, 107, 104823.	1.9	1
3	An Izhikevich Model Neuron MOS Circuit for Low Voltage Operation. Lecture Notes in Computer Science, 2019, , 718-723.	1.0	4
4	(Invited) Low-Energy Plasma Enhanced Chemical Vapor Deposition and In-Situ Doping for Junction Formation in Group-IV Semiconductor Devices. ECS Meeting Abstracts, 2019, , .	0.0	0
5	Amphiphobic Septa Enhance the Mechanical Stability of Free-Standing Bilayer Lipid Membranes. Langmuir, 2018, 34, 5615-5622.	1.6	16
6	Electrical properties and B depth profiles of in-situ B doped Si films grown by ECR Ar plasma CVD without substrate heating. Materials Science in Semiconductor Processing, 2017, 70, 50-54.	1.9	2
7	Silicon-Carbon alloy film formation on Si(100) using SiH <sub>4</sub> and CH <sub>4</sub> reaction under low-energy ECR Ar plasma irradiation. Materials Science in Semiconductor Processing, 2017, 70, 188-192.	1.9	0
8	Carrier properties of B atomic-layer-doped Si films grown by ECR Ar plasma-enhanced CVD without substrate heating. Science and Technology of Advanced Materials, 2017, 18, 294-306.	2.8	6
9	Neuro-inspired quantum associative memory using adiabatic hamiltonian evolution. , 2017, , .		1
10	Electronic properties of Si/Si-Ge Alloy/Si(100) heterostructures formed by ECR Ar plasma CVD without substrate heating. Materials Science in Semiconductor Processing, 2017, 70, 55-62.	1.9	4
11	Quantum Associative Memory with Quantum Neural Network via Adiabatic Hamiltonian Evolution. IEICE Transactions on Information and Systems, 2017, E100.D, 2683-2689.	0.4	2
12	Complexity Reduction of Neural Network Model for Local Motion Detection in Motion Stereo Vision. Lecture Notes in Computer Science, 2017, , 830-839.	1.0	0
13	C and Si delta doping in Ge by CH <sub>3</sub> SiH <sub>3</sub> using reduced pressure chemical vapor deposition. Thin Solid Films, 2016, 602, 24-28.	0.8	0
14	Effects of interfacial chemical states on the performance of perovskite solar cells. Journal of Materials Chemistry A, 2016, 4, 4392-4397.	5.2	25
15	CMOS Majority Circuit with Large Fan-In. IEICE Transactions on Electronics, 2016, E99.C, 1056-1064.	0.3	0
16	Hydrogen Atom Desorption Induced by Electron Bombardment on Si Surface. ECS Transactions, 2015, 69, 35-38.	0.3	0
17	Structure and optical properties of Si and SiGe layers grown on SiO <sub>2</sub> by chemical vapor deposition. Thin Solid Films, 2015, 579, 131-135.	0.8	14
18	Izhikevich neuron circuit using stochastic logic. Electronics Letters, 2014, 50, 1795-1797.	0.5	3

#	ARTICLE	IF	CITATIONS
19	Majority neuron circuit having large fan-in with non-volatile synaptic weight. , 2014, , .		1
20	Surface Reaction in Thin Film Formation of Si <sub>1-x</sub> Ge <sub>x</sub> Alloys on Si(100) by Electron-Cyclotron-Resonance Ar Plasma Chemical Vapor Deposition without Substrate Heating. ECS Transactions, 2014, 64, 99-105.	0.3	5
21	Atomically controlled processing for nitrogen doping of group IV semiconductors. , 2014, , .		0
22	Epitaxial growth of B-doped Si on Si(100) by electron-cyclotron-resonance Ar plasma chemical vapor deposition in a SiH <sub>4</sub> -B <sub>2</sub> H <sub>6</sub> -H <sub>2</sub> gas mixture without substrate heating. Thin Solid Films, 2014, 557, 10-13.	0.8	4
23	Epitaxial growth of Si <sub>1-x</sub> Ge <sub>x</sub> alloys and Ge on Si(100) by electron-cyclotron-resonance Ar plasma chemical vapor deposition without substrate heating. Thin Solid Films, 2014, 557, 31-35.	0.8	7
24	Nitrogen doping effect upon hole tunneling characteristics of Si barriers in Si <sub>1-x</sub> Ge <sub>x</sub> /Si resonant tunneling diode. Thin Solid Films, 2014, 557, 302-306.	0.8	1
25	(Invited) Group-IV Semiconductor Quantum Heterointegration by Low-Energy Plasma CVD Processing. ECS Transactions, 2013, 58, 195-200.	0.3	0
26	Formation and Characterization of Strained Si <sub>1-x</sub> Ge <sub>x</sub> Films Epitaxially Grown on Si(100) by Low-Energy ECR Ar Plasma CVD without Substrate Heating. ECS Transactions, 2013, 58, 207-211.	0.3	0
27	Epitaxial Growth of Heavily B-Doped Si and Ge Films on Si(100) by Low-Energy ECR Ar Plasma CVD without Substrate Heating. ECS Transactions, 2013, 58, 223-228.	0.3	3
28	(Invited) Atomically Controlled CVD Processing of Group IV Semiconductors for Strain Engineering and Doping in Ultralarge Scale Integration. ECS Transactions, 2013, 54, 55-64.	0.3	2
29	X-Ray Photoemission Study of SiO <sub>2</sub> /Si/Si <sub>0.55</sub> Ge <sub>0.45</sub> /Si Heterostructures. IEICE Transactions on Electronics, 2013, E96.C, 680-685.	0.3	1
30	Atomically controlled CVD processing of group IV semiconductors for ultra-large-scale integrations. Advances in Natural Sciences: Nanoscience and Nanotechnology, 2012, 3, 023002.	0.7	1
31	Atomically controlled CVD technology of group IV semiconductors for ultralarge scale integration. , 2012, , .		0
32	Strain Control of Si and Si <sub>1-y</sub> Cy Layers in Si/Si <sub>1-y</sub> Cy/Si(100) Heterostructures. , 2012, , .		0
33	Behavior of N atoms after thermal nitridation of Si <sub>1-x</sub> Ge <sub>x</sub> surface. Thin Solid Films, 2012, 520, 3392-3396.	0.8	2
34	Atomically Controlled Processing in Silicon-Based CVD Epitaxial Growth. Journal of Nanoscience and Nanotechnology, 2011, 11, 8348-8353.	0.9	3
35	Fabrication of high-Ge-fraction strained Si <sub>1-x</sub> Ge <sub>x</sub> /Si hole resonant tunneling diode using low-temperature Si <sub>2</sub> H <sub>6</sub> reaction for nanometer-order ultrathin Si barriers. Solid-State Electronics, 2011, 60, 112-115.	0.8	11
36	Atomically Controlled Plasma Processing for Quantum Heterointegration of Group IV Semiconductors. ECS Transactions, 2011, 41, 337-343.	0.3	0

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37	Atomically Controlled Plasma Processing for Group IV Quantum Heterostructure Formation. Key Engineering Materials, 2011, 470, 98-103.	0.4	6
38	Atomically Controlled Formation of Strained Si <sub>1-x</sub> Ge <sub>x</sub> /Si Quantum Heterostructure for Room-Temperature Resonant Tunneling Diode. ECS Transactions, 2011, 41, 309-314.	0.3	0
39	(Invited) Atomically Controlled CVD Processing for Doping in Future Si-Based Devices. ECS Transactions, 2011, 37, 181-188.	0.3	2
40	Electrical characteristics of thermal CVD B-doped Si films on highly strained Si epitaxially grown on Ge(100) by plasma CVD without substrate heating. Thin Solid Films, 2010, 518, S57-S61.	0.8	2
41	Heavy atomic-layer doping of nitrogen in Si <sub>1-x</sub> Ge film epitaxially grown on Si(100) by ultraclean low-pressure CVD. Thin Solid Films, 2010, 518, S62-S64.	0.8	4
42	Heavy B atomic-layer doping in Si epitaxial growth on Si(100) using electron-cyclotron-resonance plasma CVD. Thin Solid Films, 2010, 518, S140-S142.	0.8	4
43	Heavy carbon atomic-layer doping at Si <sub>1-x</sub> Ge/Si heterointerface. Thin Solid Films, 2010, 518, S222-S225.	0.8	8
44	Impact of Si cap layer growth on surface segregation of P incorporated by atomic layer doping. Thin Solid Films, 2010, 518, S231-S233.	0.8	7
45	Room-Temperature Resonant Tunneling Diode with High-Ge-Fraction Strained Si <sub>1-x</sub> Ge <sub>x</sub> and Nanometer-Order Ultrathin Si. ECS Transactions, 2010, 33, 379-387.	0.3	2
46	Atomically controlled plasma processing for epitaxial growth of group IV semiconductors. , 2010, , .		0
47	Atomically controlled processing in strained Si-based CVD epitaxial growth. , 2010, , .		0
48	Atomically Controlled CVD Processing for Doping of Si-Based Group IV Semiconductors. ECS Transactions, 2009, 25, 177-184.	0.3	0
49	Atomically Controlled Processing for Group IV Semiconductors. ECS Transactions, 2009, 22, 111-120.	0.3	1
50	Atomically Controlled Plasma Processing for Epitaxial Growth of Group IV Semiconductor Nanostructures. ECS Transactions, 2009, 25, 229-236.	0.3	0
51	Heavy B atomic-layer doping characteristics in Si epitaxial growth on B adsorbed Si(1 0 0) by ultraclean low-pressure CVD system. Solid-State Electronics, 2009, 53, 877-879.	0.8	11
52	Improvement in negative differential conductance characteristics of hole resonant-tunneling diodes with high Ge fraction Si/strained Si <sub>1-x</sub> Ge/Si(1 0 0) heterostructure. Solid-State Electronics, 2009, 53, 912-915.	0.8	17
53	Electrical characteristics of hole resonant tunneling diodes with high Ge fraction (x>0.4) Si/strained Si <sub>1-x</sub> Ge <sub>x</sub> /Si(100) heterostructure. Applied Surface Science, 2008, 254, 6265-6267.	3.1	4
54	Impact of Ge fraction modulation upon electrical characteristics of hole resonant tunneling diodes with Si/Strained Si <sub>1-x</sub> Ge/Si(100) heterostructure. Thin Solid Films, 2008, 517, 110-112.	0.8	6

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55	High Ge fraction intrinsic SiGe-heterochannel MOSFETs with embedded SiGe source/drain electrode formed by in-situ doped selective CVD epitaxial growth. Thin Solid Films, 2008, 517, 346-349.	0.8	7
56	Local strain in Si/Si <sub>0.6</sub> Ge <sub>0.4</sub> /Si(100) heterostructures by stripe-shape patterning. Thin Solid Films, 2008, 517, 300-302.	0.8	4
57	High-performance pMOSFETs with high Ge fraction strained SiGe-heterostructure channel and ultrashallow source/drain formed by selective B-doped SiGe CVD. Electrical Engineering in Japan (English Translation of Denki Gakkai Ronbunshi), 2008, 165, 46-50.	0.2	0
58	Behavior of N atoms in atomic-order nitrated Si <sub>0.5</sub> Ge <sub>0.5</sub> (100). Applied Surface Science, 2008, 254, 6021-6024.	3.1	3
59	Self-limited growth of Si on B atomic-layer formed Ge(100) by ultraclean low-pressure CVD system. Applied Surface Science, 2008, 254, 6090-6093.	3.1	2
60	Heavy atomic-layer doping of B in low-temperature Si epitaxial growth on Si(100) by ultraclean low-pressure chemical vapor deposition. Applied Surface Science, 2008, 254, 6086-6089.	3.1	10
61	Structural change of atomic-order nitride formed on Si <sub>1-x</sub> Ge (100) and Ge(100) by heat treatment. Thin Solid Films, 2008, 517, 219-221.	0.8	2
62	Si epitaxial growth on self-limitedly B adsorbed Si <sub>1-x</sub> Ge (100) by ultraclean low-pressure CVD system. Thin Solid Films, 2008, 517, 229-231.	0.8	4
63	Very low-temperature epitaxial growth of silicon and germanium using plasma-assisted CVD. Thin Solid Films, 2008, 517, 10-13.	0.8	14
64	Atomically controlled CVD processing for future Si-based devices. , 2008, , .		0
65	Carbon doping effect on strain relaxation during Si <sub>1-x</sub> Ge <sub>y</sub> epitaxial growth on Si(100) at 500 °C. Semiconductor Science and Technology, 2007, 22, S5-S8.	1.0	4
66	Hot Carrier Degradation of SiGe/Si Heterointerface and Experimental Estimation of Density of Locally Generated Heterointerface Traps. Japanese Journal of Applied Physics, 2007, 46, 5015.	0.8	2
67	Epitaxial growth of highly strained Si on relaxed Ge/Si(100) using ECR plasma CVD without substrate heating. Semiconductor Science and Technology, 2007, 22, S42-S45.	1.0	5
68	Strain control and electrical properties of stripe-patterned Si/Si <sub>1-x</sub> Ge/Si(100) heterostructures. Semiconductor Science and Technology, 2007, 22, S33-S37.	1.0	4
69	Hole tunnelling properties in resonant tunnelling diodes with Si/strained Si <sub>0.8</sub> Ge <sub>0.2</sub> heterostructures grown on Si(100) by low-temperature ultraclean LPCVD. Semiconductor Science and Technology, 2007, 22, S38-S41.	1.0	11
70	Epitaxial growth of P atomic layer doped Si film by alternate surface reactions of PH <sub>3</sub> and Si <sub>2</sub> H <sub>6</sub> on strained Si <sub>1-x</sub> Ge/Si(100) in ultraclean low-pressure CVD. Semiconductor Science and Technology, 2007, 22, S118-S122.	1.0	8
71	Strain Control of Si and Si <sub>1-x</sub> Ge <sub>x</sub> Layers in the Si/Si <sub>1-x</sub> Ge <sub>x</sub> /Si Heterostructures by Stripe-Shape Patterning for Future Si-Based Devices. ECS Transactions, 2007, 11, 91-99.	0.3	0
72	Fabrication of Hole Resonant Tunneling Diodes with Nanometer Order Heterostructures of Si/Strained Si <sub>1-x</sub> Ge <sub>x</sub> Epitaxially Grown on Si(100). ECS Transactions, 2007, 11, 131-139.	0.3	5

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73	Atomically Controlled Processing for Group IV Semiconductors by Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2006, 45, 6767-6785.	0.8	84
74	High Performance pMOSFETs with High Ge Fraction Strained SiGe-heterostructure-channel and Ultrashallow Source/Drain Formed by Selective B-Doped SiGe CVD. IEEJ Transactions on Electronics, Information and Systems, 2006, 126, 1079-1082.	0.1	0
75	Carbon effect on strain compensation in Si <sub>1-x</sub> Ge <sub>y</sub> films epitaxially grown on Si(100). Thin Solid Films, 2006, 508, 140-142.	0.8	7
76	Photo detection characteristics of Si/Si <sub>1-x</sub> Ge <sub>y</sub> /Si p-i-n diodes integrated with optical waveguides. Thin Solid Films, 2006, 508, 399-401.	0.8	7
77	Surface reaction and B atom segregation in ECR chlorine plasma etching of B-doped Si <sub>1-x</sub> Ge <sub>y</sub> epitaxial films. Thin Solid Films, 2006, 508, 301-304.	0.8	0
78	Characterization of hot-carrier degraded SiGe/Si-hetero-PMOSFETs. Thin Solid Films, 2006, 508, 326-328.	0.8	4
79	Effect of grain boundary on electrical characteristics in B- and P-doped polycrystalline Si <sub>1-x</sub> Ge <sub>y</sub> film deposited by ultraclean LPCVD. Thin Solid Films, 2006, 508, 36-39.	0.8	4
80	Thermal effect on strain relaxation in Ge films epitaxially grown on Si(100) using ECR plasma CVD. Thin Solid Films, 2006, 508, 143-146.	0.8	13
81	Strain relaxation by stripe patterning in Si/Si <sub>1-x</sub> Ge <sub>y</sub> /Si(100) heterostructures. Thin Solid Films, 2006, 508, 239-242.	0.8	13
82	Strain Control of Stripe Patterned Si/Si <sub>1-x</sub> Ge <sub>y</sub> /Si(100) Heterostructures. ECS Transactions, 2006, 3, 421-427.	0.3	1
83	A Study on B Atomic Layer Formation for B-Doped Si <sub>1-x</sub> Ge <sub>y</sub> (100) Epitaxial Growth Using Ultraclean LPCVD System. ECS Transactions, 2006, 3, 861-866.	0.3	2
84	Atomic-Order Thermal Nitridation of Si <sub>1-x</sub> Ge <sub>y</sub> (100) at Low Temperatures by NH <sub>3</sub> . ECS Transactions, 2006, 3, 1205-1210.	0.3	0
85	Atomically controlled CVD technology for group IV semiconductors. , 2006, , .		0
86	Sidewall protection by nitrogen and oxygen in poly-Si <sub>1-x</sub> Ge <sub>y</sub> anisotropic etching using Cl <sub>2</sub> /N <sub>2</sub> /O <sub>2</sub> plasma. Materials Science in Semiconductor Processing, 2005, 8, 239-243.	1.9	6
87	Atomically controlled Ge epitaxial growth on Si(100) in Ar-plasma-enhanced GeH <sub>4</sub> reaction. Materials Science in Semiconductor Processing, 2005, 8, 69-72.	1.9	10
88	Integration of Si p-i-n diodes for light emitter and detector with optical waveguides. Materials Science in Semiconductor Processing, 2005, 8, 435-438.	1.9	6
89	Electrical properties of W delta doped Si epitaxial films grown on Si(100) by ultraclean low-pressure chemical vapor deposition. Materials Science in Semiconductor Processing, 2005, 8, 125-129.	1.9	2
90	Electrical properties of N atomic layer doped Si epitaxial films grown by ultraclean low-pressure chemical vapor deposition. Materials Science in Semiconductor Processing, 2005, 8, 121-124.	1.9	5

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91	Si epitaxial growth on atomic-order nitrided Si(1 0 0) using electron cyclotron resonance plasma. Materials Science in Semiconductor Processing, 2005, 8, 65-68.	1.9	2
92	Separation by bonding Si Islands (SBSI) for LSI applications. Materials Science in Semiconductor Processing, 2005, 8, 59-63.	1.9	0
93	SiGe <sub>0.3</sub> epitaxial growth on Si(1 0 0) by alternately supplied NH <sub>3</sub> and SiH <sub>4</sub> . Shinku/Journal of the Vacuum Society of Japan, 2005, 48, 8-12.		0
94	Separation by Bonding Si Islands (SBSI) for Advanced CMOS LSI Applications. IEICE Transactions on Electronics, 2005, E88-C, 656-661.	0.3	0
95	Atomically Controlled Technology for Future Si-Based Devices. Solid State Phenomena, 2004, 95-96, 607-616.	0.3	15
96	Atomically Controlled Impurity Doping in Si-Based CVD Epitaxial Growth. Materials Research Society Symposia Proceedings, 2004, 809, B10.1.1.	0.1	3
97	Si self-diffusivity using isotopically pure <sup>30</sup> Si epitaxial layers. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2004, 114-115, 330-333.	1.7	15
98	Epitaxial growth of N delta doped Si films on Si(1 0 0) by alternately supplied NH <sub>3</sub> and SiH <sub>4</sub> . Applied Surface Science, 2004, 224, 197-201.	3.1	7
99	Relationship between impurity (B or P) and carrier concentration in SiGe(C) epitaxial film produced by thermal treatment. Applied Surface Science, 2004, 224, 77-81.	3.1	8
100	Proposal of a multi-layer channel MOSFET: the application of selective etching for Si/SiGe stacked layers. Applied Surface Science, 2004, 224, 270-273.	3.1	4
101	Formation of heavily P-doped Si epitaxial film on Si(100) by multiple atomic-layer doping technique. Applied Surface Science, 2004, 224, 202-205.	3.1	18
102	Effect of carbon on the thermal stability of a Si atomic layer on Ge(1 0 0). Applied Surface Science, 2004, 224, 206-209.	3.1	3
103	Ar plasma irradiation effects in atomically controlled Si epitaxial growth. Applied Surface Science, 2004, 224, 210-214.	3.1	10
104	Fabrication of 0.12 μm pMOSFETs on high Ge fraction Si/Si <sub>1-x</sub> Ge <sub>x</sub> /Si(1 0 0) heterostructure with ultrashallow source/drain formed using B-doped SiGe CVD. Applied Surface Science, 2004, 224, 254-259.	3.1	11
105	Contact resistivity between tungsten and impurity (P and B)-doped Si <sub>1-x</sub> Ge <sub>x</sub> C epitaxial layer. Applied Surface Science, 2003, 212-213, 679-683.	3.1	13
106	Si epitaxial growth on SiH <sub>3</sub> CH <sub>3</sub> reacted Ge(1 0 0) and intermixing between Si and Ge during heat treatment. Applied Surface Science, 2003, 212-213, 193-196.	3.1	4
107	Si atomic layer-by-layer epitaxial growth process using alternate exposure of Si(1 0 0) to SiH <sub>4</sub> and to Ar plasma. Applied Surface Science, 2003, 212-213, 197-200.	3.1	6
108	Work function of impurity-doped polycrystalline Si <sub>1-x</sub> Ge <sub>x</sub> C film deposited by ultraclean low-pressure CVD. Applied Surface Science, 2003, 212-213, 209-212.	3.1	3

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109	W delta doping in Si(1 0 0) using ultraclean low-pressure CVD. Applied Surface Science, 2003, 212-213, 684-688.	3.1	4
110	Atomic-layer doping in Si by alternately supplied NH <sub>3</sub> and SiH <sub>4</sub> . Applied Physics Letters, 2003, 82, 3472-3474.	1.5	21
111	Heavy Doping Characteristics of Si Films Epitaxially Grown at 450Å°C by Alternately Supplied PH <sub>3</sub> and SiH <sub>4</sub> . , 2003, , 145-150.		0
112	Si Epitaxial Growth on the Atomic-Order Nitrided Si(100) Surface in SiH <sub>4</sub> Reaction. , 2003, , 139-144.		1
113	Atomically controlled processing for group IV semiconductors. Surface and Interface Analysis, 2002, 34, 423-431.	0.8	40
114	Super self-aligned technology of ultra-shallow junction in MOSFETs using selective Si <sub>1-<math>\lambda</math></sub> Ge <sub><math>\lambda</math></sub> CVD. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 89, 120-124.	1.7	7
115	Thermal nitridation of ultrathin SiO <sub>2</sub> on Si by NH <sub>3</sub> . Surface and Interface Analysis, 2002, 34, 456-459.	0.8	25
116	Phosphorus Doping in Si <sub>1-x-y</sub> Ge <sub>y</sub> Cy Epitaxial Growth by Low-Pressure Chemical Vapor Deposition Using a SiH <sub>4</sub> -GeH <sub>4</sub> -CH <sub>3</sub> SiH <sub>3</sub> -PH <sub>3</sub> -H <sub>2</sub> Gas System. Japanese Journal of Applied Physics, 2001, 40, 2697-2700.	0.8	9
117	Atomic-order thermal nitridation of Si(100) and subsequent growth of Si. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2001, 19, 1907-1911.	0.9	9
118	Observation of sharp current peaks in resonant tunneling diode with strained Si <sub>0.6</sub> Ge <sub>0.4</sub> /Si(100) grown by low-temperature low-pressure CVD. Journal of Crystal Growth, 2000, 209, 315-320.	0.7	15
119	Epitaxial growth of Si <sub>1-<math>\lambda</math></sub> Ge <sub><math>\lambda</math></sub> C <sub>y</sub> film on Si(100) in a SiH <sub>4</sub> -GeH <sub>4</sub> -CH <sub>3</sub> SiH <sub>3</sub> reaction. Thin Solid Films, 2000, 369, 167-170.	0.8	18
120	Segregation and diffusion of impurities from doped Si <sub>1-<math>\lambda</math></sub> Ge <sub><math>\lambda</math></sub> films into silicon. Thin Solid Films, 2000, 369, 222-225.	0.8	10
121	Drain leakage current and instability of drain current in Si/Si <sub>1-<math>\lambda</math></sub> Ge <sub><math>\lambda</math></sub> MOSFETs. Thin Solid Films, 2000, 369, 379-382.	0.8	5
122	Doping and electrical characteristics of in-situ heavily B-doped Si <sub>1-<math>\lambda</math></sub> Ge <sub><math>\lambda</math></sub> Cy films epitaxially grown using ultraclean LPCVD. Thin Solid Films, 2000, 380, 57-60.	0.8	23
123	Atomic-layer doping in Si by alternately supplied PH <sub>3</sub> and SiH <sub>4</sub> . Thin Solid Films, 2000, 380, 134-136.	0.8	18
124	Atomic-layer adsorption of P on Si(100) and Ge(100) by PH <sub>3</sub> using an ultraclean low-pressure chemical vapor deposition. Applied Surface Science, 2000, 162-163, 390-394.	3.1	25
125	Surface reaction of CH <sub>3</sub> SiH <sub>3</sub> on Ge(100) and Si(100). Applied Surface Science, 2000, 162-163, 156-160.	3.1	19
126	Effect of Si/Si <sub>1-x</sub> Ge <sub>x</sub> /Si Barriers on the Characteristics of Si <sub>1-x</sub> Ge <sub>x</sub> /Si Resonant Tunneling Structures. Chinese Physics Letters, 2000, 17, 844-846.	1.3	3



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127	Separation between Surface Adsorption and Reaction of NH <sub>3</sub> on Si(100) by Flash Heating. Japanese Journal of Applied Physics, 1999, 38, 515-517.	0.8	26
128	Segregation and diffusion of phosphorus from doped Si <sub>1-x</sub> Ge <sub>x</sub> films into silicon. Journal of Applied Physics, 1999, 86, 5480-5483.	1.1	14
129	Doping and electrical characteristics of in situ heavily B-doped Si <sub>1-x</sub> Ge <sub>x</sub> films epitaxially grown using ultraclean LPCVD. Thin Solid Films, 1999, 343-344, 541-544.	0.8	15
130	Layer-by-layer growth of silicon nitride films by NH <sub>3</sub> and SiH <sub>4</sub> . European Physical Journal Special Topics, 1999, 09, Pr8-333-Pr8-340.	0.2	4
131	Low-temperature reaction of CH <sub>4</sub> on Si(100). Journal of Crystal Growth, 1998, 188, 131-136.	0.7	21
132	Atomic-Order Thermal Nitridation of Silicon at Low Temperatures. Journal of the Electrochemical Society, 1998, 145, 4252-4256.	1.3	35
133	Atomic-Layer Surface Reaction of SiH <sub>4</sub> on Ge(100). Japanese Journal of Applied Physics, 1997, 36, 4042-4045.	0.8	16
134	Initial growth characteristics of germanium on silicon in LPCVD using germane gas. Journal of Crystal Growth, 1997, 174, 686-690.	0.7	19
135	Atomic Layer-by-Layer Epitaxy of Silicon and Germanium Using Flash Heating in CVD. European Physical Journal Special Topics, 1995, 05, C5-1101-C5-1108.	0.2	6
136	Stability of the dimer structure formed on Si(100) by ultraclean low-pressure chemical-vapor deposition. Journal of Applied Physics, 1994, 75, 3701-3703.	1.1	40
137	Atomic-layer epitaxy control of Ge and Si in flash-heating CVD using GeH <sub>4</sub> and SiH <sub>4</sub> gases. Applied Surface Science, 1994, 82-83, 354-358.	3.1	24
138	Silicon atomic layer growth controlled by flash heating in chemical vapor deposition using SiH <sub>4</sub> gas. Applied Physics Letters, 1993, 62, 2353-2355.	1.5	45
139	Silicon atomic layer growth using flash heating in CVD. European Physical Journal Special Topics, 1993, 03, C3-449-C3-456.	0.2	1
140	Atomic layer epitaxy of germanium on silicon using flash heating chemical vapor deposition. Journal of Crystal Growth, 1991, 115, 79-82.	0.7	25
141	Capture/Emission Processes of Carriers in Heterointerface Traps Observed in the Transient Charge-Pumping Characteristics of SiGe/Si-Hetero-Channel pMOSFETs. Key Engineering Materials, 0, 470, 201-206.	0.4	2